CLAIMS

- 1. An ID label comprising:
- a label substratum over which an antenna is formed;
- a thin film integrated circuit device including a thin film transistor, provided in contact with the label substratum;
 - a separating sheet; and
 - an adhesive provided between the label substratum and the separating sheet.
- 2. The ID label according to claim 1, wherein the antenna and the thin film integrated circuit device are connected through a cross wiring.
- 3. The ID label according to claim 1, wherein a protective layer comprising a single layer or stacked layers containing silicon oxide, silicon nitride or silicon oxynitride is formed on at least one of an upper surface and a lower surface of the thin film integrated circuit device.
- 4. The ID label according to claim 1, wherein in the case where the protective layer is formed on the upper surface and the lower surface of the thin film 20 integrated circuit device, it is placed the thin film integrated circuit device at a position of $(d/2) \pm 30 \mu m$ or less when a total thickness of the thin film integrated circuit device and the top and bottom protective films is d.
- 5. The ID label according to claim 1, wherein a semiconductor film of the thin film transistor included in the thin film integrated circuit device contains hydrogen or halogen of 0.0005 to 5 atomic %.
 - 6. The ID label according to claim 1, wherein a size of the thin film integrated circuit device is 0.09 to 25 mm²,

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- 7. The ID label according to claim 1, wherein a thickness of the thin film integrated circuit device is 0.1 to 3 μ m.
 - 8. An ID label comprising:
 - an internal substratum over which an antenna is formed;
 - a label substratum;
- a thin film integrated circuit device including a thin film transistor, provided in contact with the internal substratum;
 - a separating sheet; and
- an adhesive provided between the label substratum and the separating sheet.
 - 9. The ID label according to claim 8, wherein the antenna and the thin film integrated circuit device are connected through a cross wiring.
- 10. The ID label according to claim 8, wherein a protective layer comprising a single layer or stacked layers containing silicon oxide, silicon nitride or silicon oxynitride is formed on at least one of an upper portion and a lower portion of the thin film integrated circuit device.
- 11. The ID label according to claim 8, wherein in the case where the protective layer is formed on the upper surface and the lower surface of the thin film integrated circuit device, it is placed the thin film integrated circuit device at a position of $(d/2) \pm 30 \,\mu m$ or less when a total thickness of the thin film integrated circuit device and the top and bottom protective films is d.

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- 12. The ID label according to claim 8, wherein a semiconductor film of the thin film transistor included in the thin film integrated circuit device contains hydrogen or halogen of 0.0005 to 5 atomic %.
 - 13. The ID label according to claim 8, wherein a size of the thin film

integrated circuit device is 0.09 to 25 mm²,

14. The ID label according to claim 8, wherein a thickness of the thin film integrated circuit device is 0.1 to 3 μ m.

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15. An ID card comprising:

- a card substratum over which an antenna is formed;
- a thin film integrated circuit device including a thin film transistor, provided in contact with card substratum;
- and the thin film integrated circuit device are formed.
 - 16. The ID card according to claim 15, wherein the antenna and the thin film integrated circuit device are connected through a cross wiring.

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- 17. The ID card according to claim 15, wherein the cover comprises resin and is formed by a laminating method.
- 18. The ID card according to claim 15, wherein a protective layer comprising 20 a single layer or stacked layers containing silicon oxide, silicon nitride or silicon oxynitride is formed on at least one of the upper surface and the lower surface of the thin film integrated circuit device.

19. An ID card comprising:

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an internal substratum over which an antenna is formed;

- a thin film integrated circuit device including a thin film transistor, provided in contact with the internal substratum;
 - a cover for covering around the internal substratum.
- 30 20. The ID card according to claim 19, wherein the antenna and the thin film

integrated circuit device are connected through a cross wiring.

21. The ID card according to claim 19, wherein the cover comprises resin and is formed by a laminating method.

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22. The ID card according to claim 19, wherein a protective layer comprising a single layer or stacked layers containing silicon oxide, silicon nitride or silicon oxynitride is formed on at least one of the upper surface and the lower surface of the thin film integrated circuit device.

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23. An ID tag comprising:

a thin film integrated circuit including a thin film transistor provided in contact with a substratum on which an antenna is formed; and

a cover for covering at least a side in which the antenna and the thin film integrated circuit device are formed in the substratum.

- 24. The ID tag according to claim 23, wherein the antenna and the thin film integrated circuit device are connected through a cross wiring.
- 25. The ID tag according to claim 23, wherein the cover comprises resin and is formed by a laminating method.
- 26. The ID tag according to claim 23, wherein a protective layer comprising a single layer of stacked layers containing silicon oxide, silicon nitride of silicon oxynitride is formed on at least one of the upper surface and the lower surface of the thin film integrated circuit device.

27. An ID tag comprising:

a thin film integrated circuit device including a thin film transistor provided 30 in contact with an internal substratum on which an antenna is formed; and a cover for covering around the internal substratum.

28. The ID tag according to claim 27, wherein the antenna and the thin film integrated circuit device are connected through a cross wiring.

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- 29. The ID tag according to claim 27, wherein the cover comprises resin and is formed by a laminating method.
- 30. The ID tag according to claim 27, wherein a protective layer comprising a single layer of stacked layers containing silicon oxide, silicon nitride of silicon oxynitride is formed on at least one of the upper surface and the lower surface of the thin film integrated circuit device.

31. An object comprising:

a thin film integrated circuit device including a thin film transistor provided in contact with a substratum on which an antenna is formed; and

a cover for covering at least a side in which an antenna and the thin film integrated circuit device are formed.

32. The object according to claim 31, wherein a protective layer comprising a single layer or stacked layers containing silicon oxide, silicon nitride or silicon oxynitride is formed on at least one of the upper surface and the lower surface of the thin film integrated circuit device.

33. An object comprising:

- a thin film integrated circuit device including a thin film transistor provided in contact with an internal substratum on which an antenna is formed; and a cover for covering around the internal substratum.
 - 34. The object according to claim 33, wherein a protective layer comprising a

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single layer or stacked layers containing silicon oxide, silicon nitride or silicon oxynitride is formed on at least one of the upper surface and the lower surface of the thin film integrated circuit device.

35. An ID label comprising:

a label substratum having a first surface and a second surface opposing to the first surface;

an antenna formed over the first surface of the label substratum;

a thin film integrated circuit device including a thin film transistor, over the 10 first surface of the label substratum;

a wiring formed on the second surface of the label substratum;

a separating sheet provided over the first surface of the label substratum with an adhesive layer, antenna, and the thin film integrated circuit device interposed therebetween,

wherein the wiring electrically connect the thin film transistor and a part of the antenna through a contact hole formed in the label substratum.

36. An ID label comprising:

a label substratum;

an antenna formed over the label substratum;

an insulating layer over the antenna;

a wiring formed on the insulating layer;

a thin film integrated circuit device including a thin film transistor, over the label substratum;

a separating sheet provided over the label substratum with an adhesive layer, the antenna, and insulating layer, and the thin film integrated circuit device interposed therebetween,

wherein the wiring is connected to the antenna through a contact hoe formed in the insulating layer.